CLAIMS

1. A polishing pad having a polishing layer,

the polishing layer comprising a product of curing reaction of a polyurethane-forming raw material composition containing: (A) an isocyanate-terminated prepolymer obtained by reaction of a prepolymer-forming raw material composition (a) containing an isocyanate component and a polyester-based polyol; (B) an isocyanate-terminated prepolymer obtained by reaction of a prepolymer-forming raw material composition (b) containing an isocyanate component and a polyether-based polyol; and a chain extender, wherein the product of curing reaction has a phase-separated structure.

2. The polishing pad according to claim 1, wherein the phase-separated structure has island and sea components, wherein the island component has an average maximum length of 0.5 μm to 100 μm.

3. The polishing pad according to claim 1, wherein the total content of an oxycarbonyl group constituting the polyester-based polyol is from 8 to 43% by weight based on the total weight of high-molecular weight polyols in the prepolymer-forming raw material compositions (a) and (b).

4. The polishing pad according to claim 1, wherein the polyester-based polyol is at least one selected from the group consisting of polyethylene adipate glycol, polybutylene adipate glycol, and polyhexamethylene adipate glycol.

5. The polishing pad according to claim 1, wherein the polyether-based polyol is polytetramethylene ether glycol.

6. A method for manufacturing a semiconductor device, comprising the step of polishing a surface of a semiconductor wafer using the polishing pad according to claim 1.

CLAIMS

The invention claimed is:

1. A polishing pad having a polishing layer, the polishing layer comprising a product of curing reaction of a polyurethane-forming raw material composition containing: an isocyanate-terminated prepolymer (A) obtained by reaction of a prepolymer-forming raw material composition (a) containing an isocyanate component and a polyester-based polyol; an isocyanate-terminated prepolymer (B) obtained by reaction of a prepolymer-forming raw material composition (b) containing an isocyanate component and a polyether-based polyol; and a chain extender, wherein the product of curing reaction has a phase-separated structure, wherein an amount of the isocyanate-terminated prepolymer (A) is from 15 to 570 parts by weight based on 100 parts by weight of the isocyanate-terminated prepolymer (B).

2. The polishing pad according to claim 1, wherein the phase-separated structure has island and sea components, wherein the island component has an average maximum length of 0.5 μm to 100 μm.

3. The polishing pad according to claim 1, wherein the total content of an oxycarbonyl group constituting the polyester-based polyol is from 8 to 43% by weight based on the total weight of high-molecular weight polyols in the prepolymer-forming raw material compositions (a) and (b).

4. The polishing pad according to claim 1, wherein the polyester-based polyol is at least one selected from the group consisting of polyethylene adipate glycol, polybutylene adipate glycol, and polyhexamethylene adipate glycol.

5. The polishing pad according to claim 1, wherein the polyether-based polyol is polytetramethylene ether glycol.

6. A method for manufacturing a semiconductor device, comprising the step of polishing a surface of a semiconductor wafer using the polishing pad according to claim 1.